



## Non-Collinear Antiferromagnets For High Density And Low Power Spintronics Devices

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### The Invention

Spintronic devices based on metallic antiferromagnets having a non-collinear spin structure are provided. Also provided are methods for operating the devices. The spintronic devices are based on a bilayer structure that includes a spin torque layer of an antiferromagnetic material having a non-collinear triangular spin structure adjoining a layer of ferromagnetic material.

### Additional Information

#### For More Information About the Inventors

- [Chang-Beom Eom](#)

#### Tech Fields

- [Information Technology : Hardware](#)
- [Materials & Chemicals : Composites](#)

For current licensing status, please contact Michael Carey at [mcarey@warf.org](mailto:mcarey@warf.org) or 608-960-9867